"Yب / Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

◕ È / Features

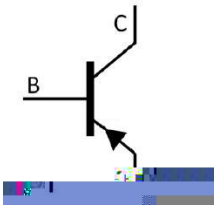
h_{FE} $V_{CE(sat)}$

High DC Current Gain, Low Collector to Emitter Saturation Voltage.

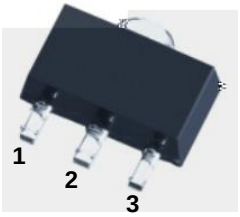
¥ ¸ / Applications

General purpose amplifier and switching.

Л ف̃ ǫ̃ ≠ ɛ / Equivalent Circuit



ã ﾒ ŭ̃ / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

ł. ʜ J̇ / Marking

h_{FE} Range	100 300
Marking	H2A

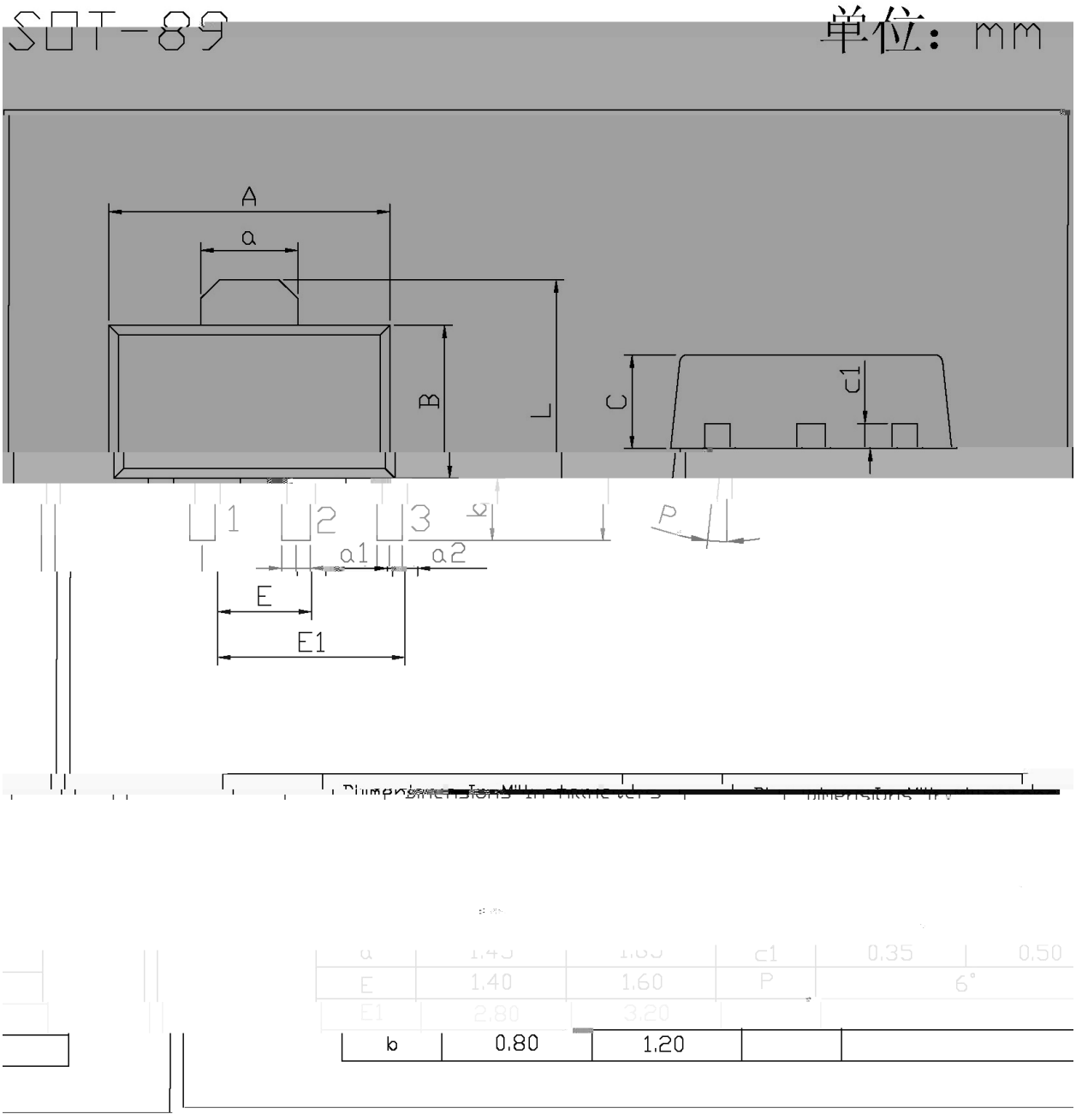
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	450	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}					

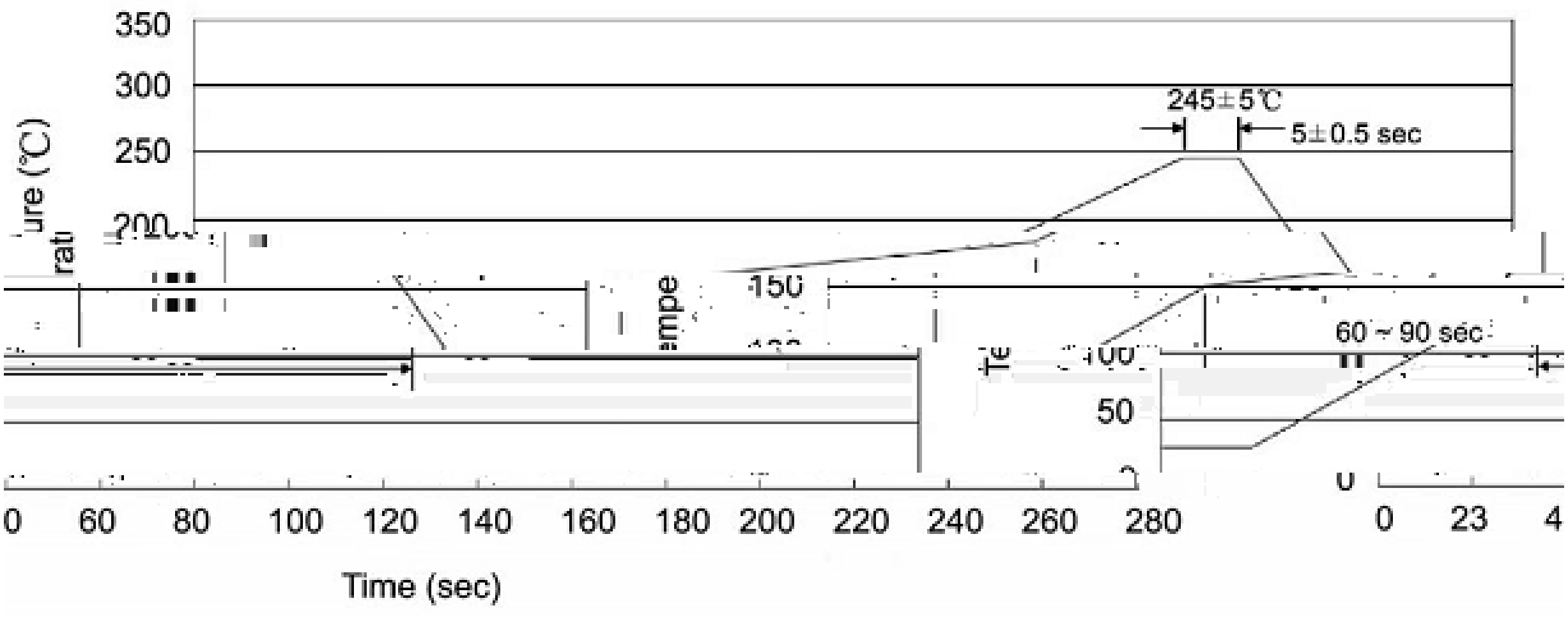
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

≠ ∃ ℀Ą´E ∀ ∱ / Electrical Characteristic Curve

ᵘ ĖÒĻ ʃ / Package Dimensions



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	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.